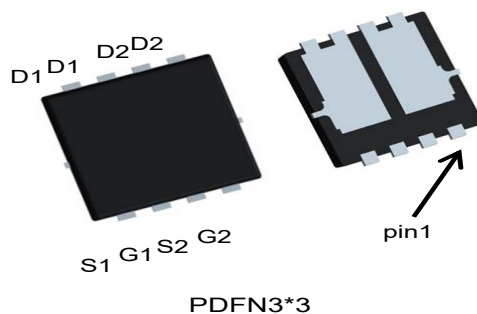


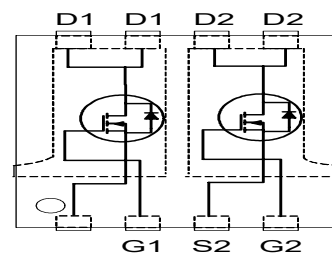
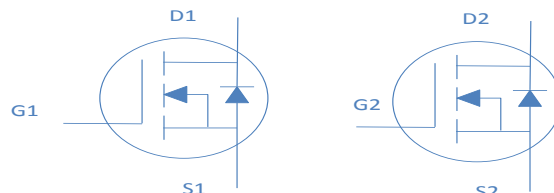
Features

- 20V/25A,
 $R_{DS(ON)} = 4.5m\Omega(\text{typ.}) @ V_{GS} = 10V$
 $R_{DS(ON)} = 6.5m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)



Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.



S1

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	25	A
Pulsed Drain Current	I_{DM}	64	A
Maximum Power Dissipation	P_D	5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	42	$^\circ\text{C/W}$
-------------------------------------------------------------	-----------------	----	--------------------

20V N+N-Channel Enhancement Mode MOSFET

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

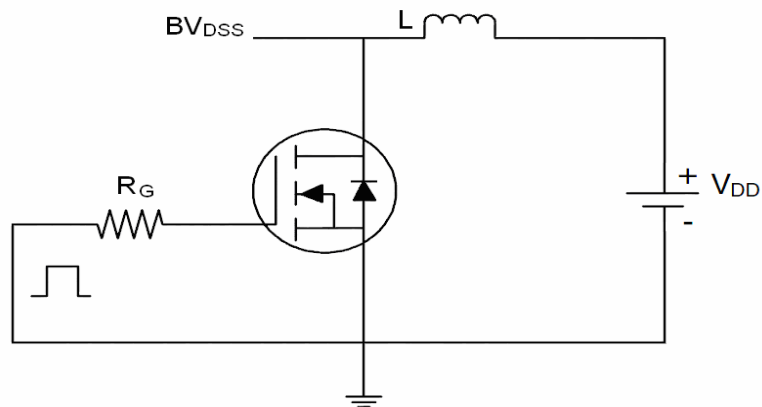
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	0.8	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=10A$	-	4.5	7	m Ω
		$V_{GS}=2.5V, I_D=5.5A$	-	5	8.5	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=10A$	30	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1306	-	PF
Output Capacitance	C_{OSS}		-	228	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	200	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	2.5	-	nS
Turn-on Rise Time	t_r		-	7.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	49	-	nS
Turn-Off Fall Time	t_f		-	10.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=10A,$ $V_{GS}=4.5V$	-	17.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	4.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	25	A

Notes:

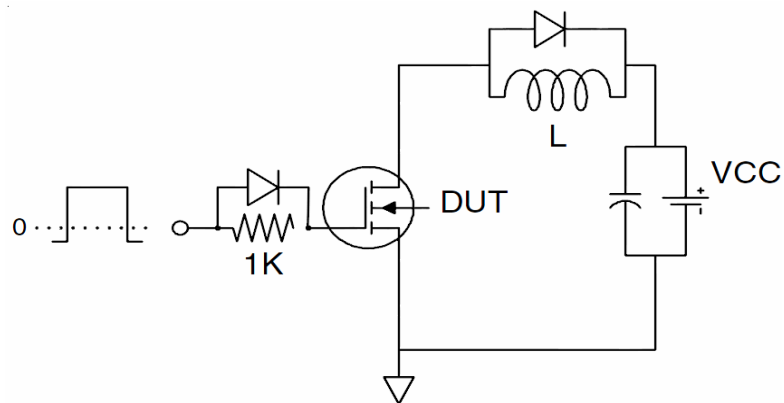
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

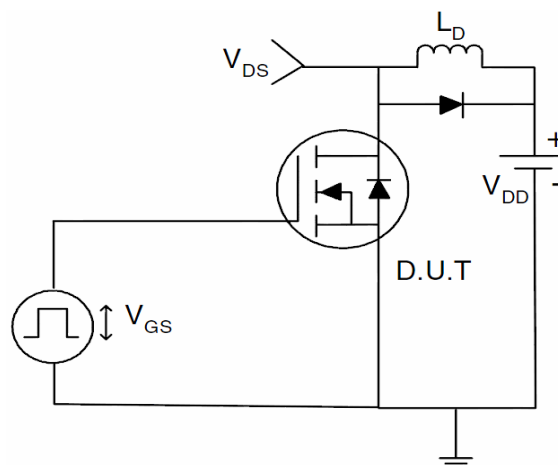
1) E_{AS} test Circuits



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

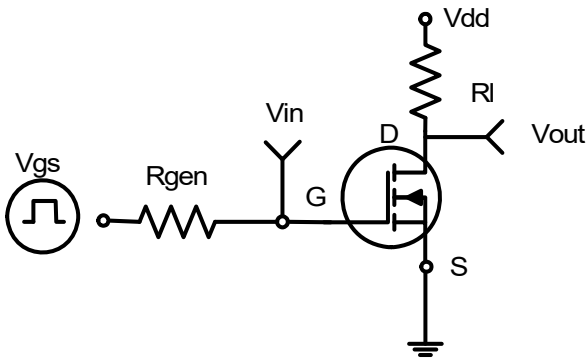


Figure 1: Switching Test Circuit

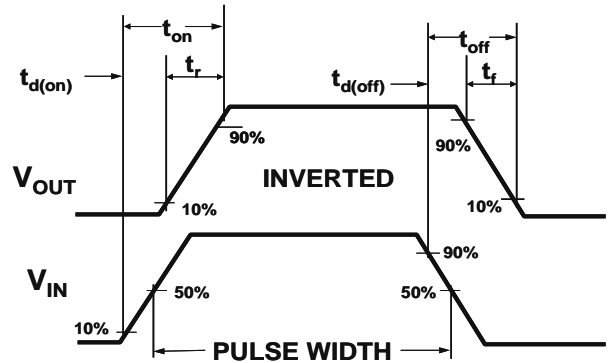


Figure 2: Switching Waveforms

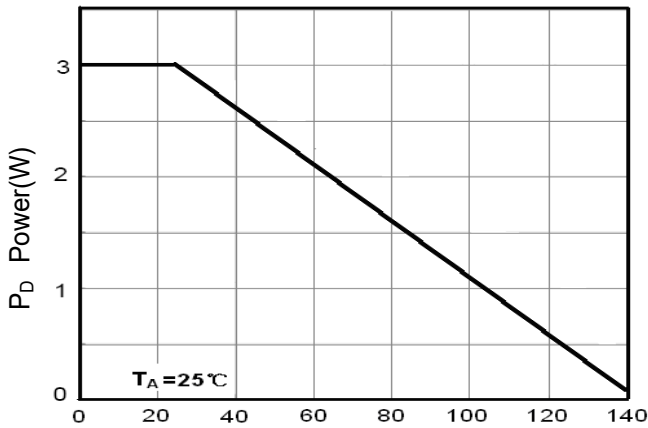


Figure 3 Power Dissipation

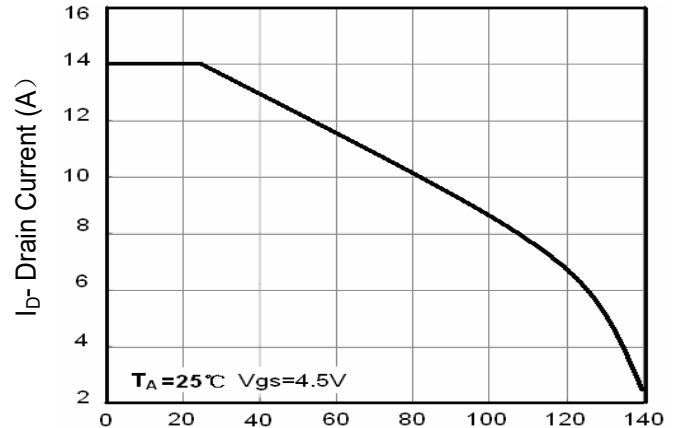


Figure 4 Drain Current

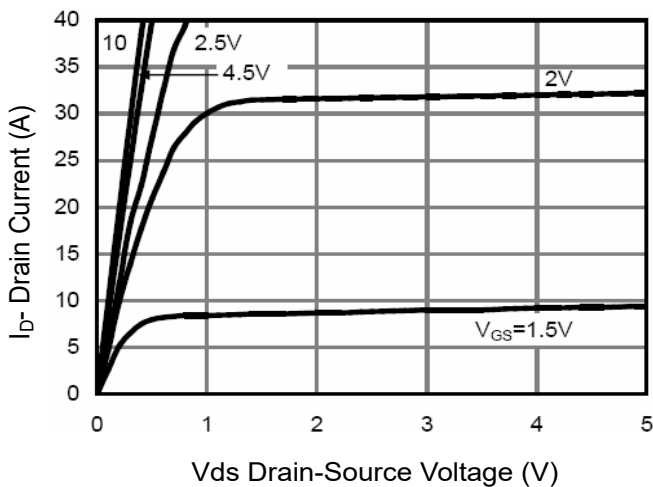


Figure 5 Output Characteristics

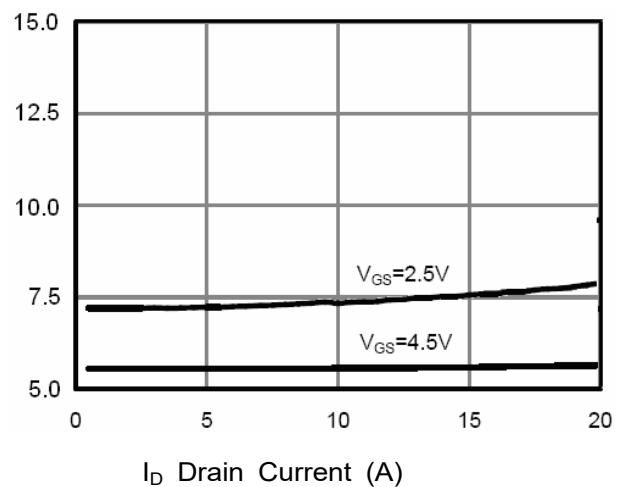


Figure 6 Drain-Source On-Resistance

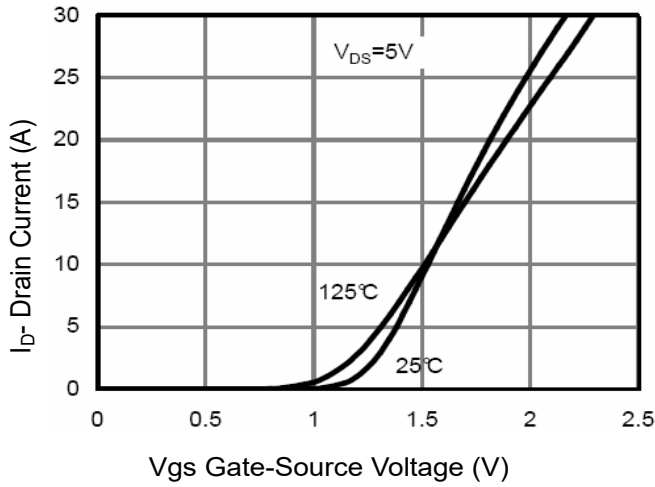


Figure 7 Transfer Characteristics

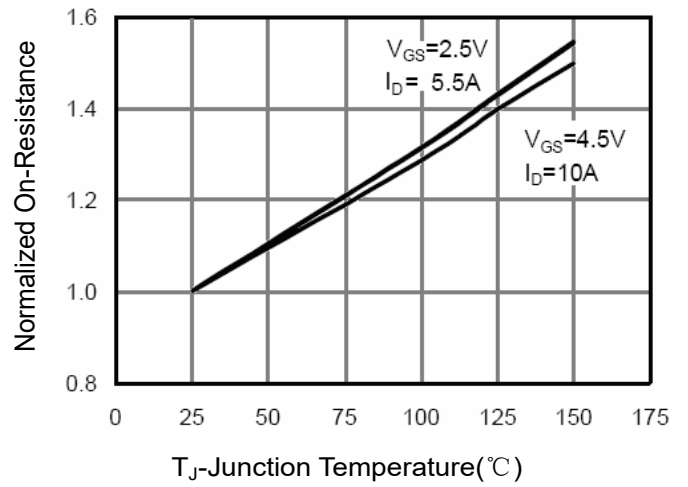


Figure 8 Drain-Source On-Resistance

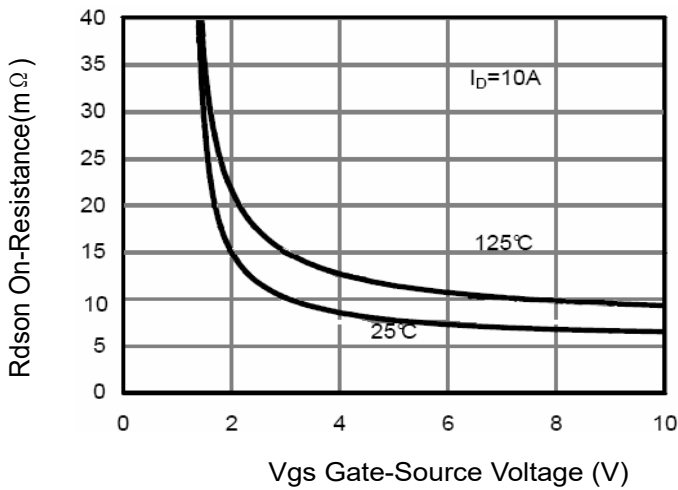


Figure 9 Rdson vs Vgs

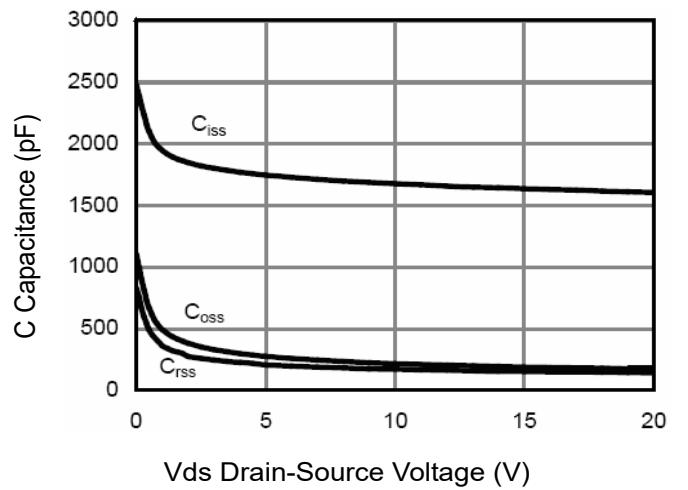


Figure 10 Capacitance vs Vds

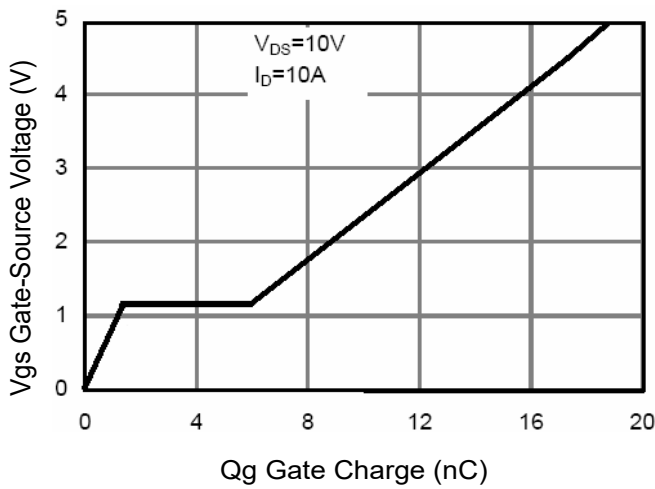


Figure 11 Gate Charge

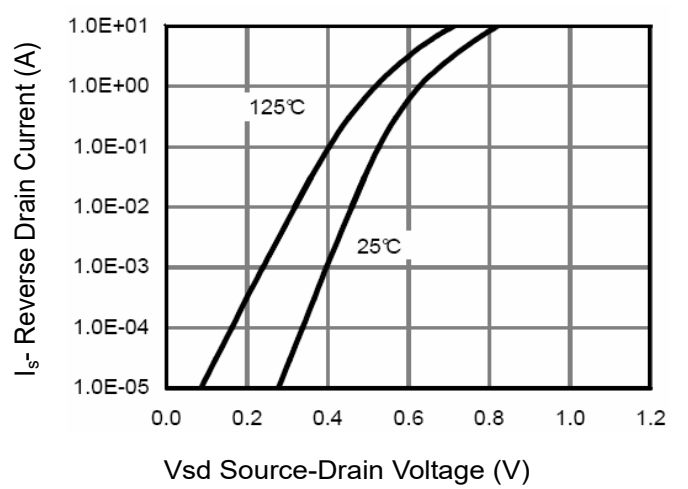


Figure 12 Source- Drain Diode Forward

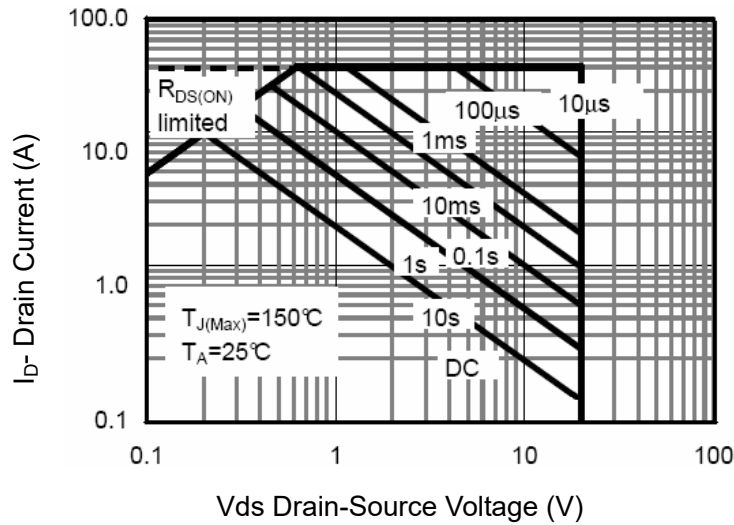


Figure 13 Safe Operation Area

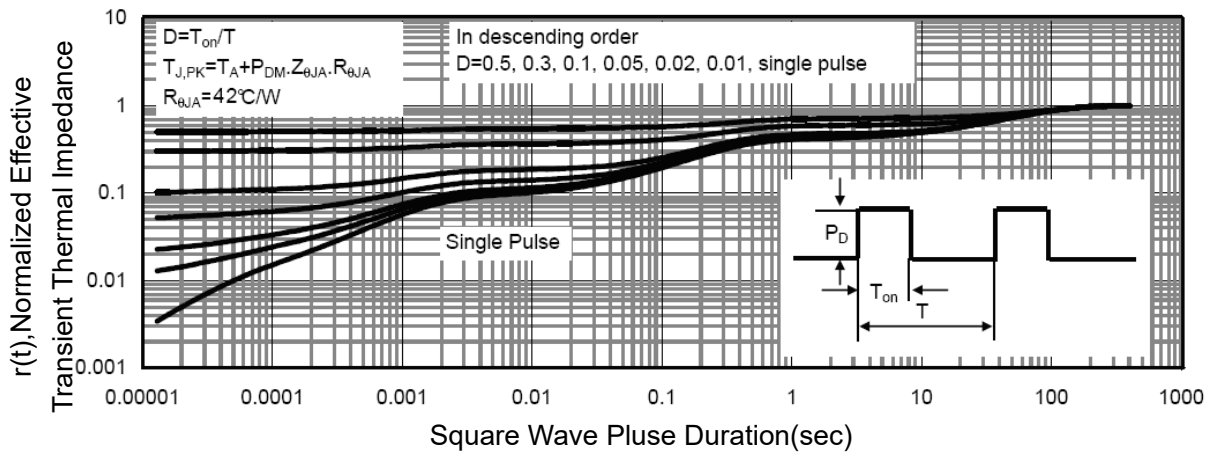


Figure 14 Normalized Maximum Transient Thermal Impedance

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1 sec
Pb-Free device	260°C +0/-5°C	5sec ±1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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